

**RESPONSE ACCOMPANYING REQUEST FOR CONTINUED EXAMINATION**  
**Serial No. 10/672,002**  
**Page 2 of 6**

**IN THE CLAIMS**

36. (Cancelled)

37. (Currently Amended) A method for etching a substrate, comprising:  
(a) etching the substrate in a first step, wherein the first step comprises:  
supplying a first etch gas at a first rate to a first portion of the substrate through a first flow channel; and  
supplying the first etch gas at a second rate to a second portion of the substrate through a second flow channel, wherein the first rate is different than the second rate, and wherein the first portion is different from the second portion; and  
(b) etching the substrate in a second step, wherein the first step is different from the second step, and wherein the second step comprises:  
supplying a second etch gas at a third rate to the first portion of the substrate through the first flow channel; and  
supplying the second etch gas at a fourth rate to the second portion of the substrate through the second flow channel, wherein the third rate is different than the fourth rate.

38. (Previously Presented) The method of claim 37, wherein the first gas is different than the second gas.

39. (Previously Presented) The method of claim 37, wherein the first rate is greater than the second rate.

40. (Previously Presented) The method of claim 37, wherein the first rate is less than the second rate.

41. (Previously Presented) The method of claim 37, wherein the third rate is greater than the fourth rate.

**RESPONSE ACCOMPANYING REQUEST FOR CONTINUED EXAMINATION**  
**Serial No. 10/672,002**  
**Page 3 of 6**

42. (Previously Presented) The method of claim 37, wherein the third rate is less than the fourth rate.

43. (Previously Presented) The method of claim 37, further comprising:  
supplying the first gas to the first portion for a first period of time; and  
supplying the first gas to the second portion for a second period of time  
that is different than the first period of time.

44. (Previously Presented) The method of claim 37, further comprising:  
supplying the second gas to the first portion for a first period of time; and  
supplying the second gas to the second portion for a second period of  
time that is different than the first period of time.

45. (Previously Presented) The method of claim 37, wherein the first portion is an inner portion of the substrate and the second portion is an outer portion of the substrate.

46. (Previously Presented) The method of claim 37, further comprising:  
supplying the first gas to at least a third portion of the substrate.

47. (Previously Presented) The method of claim 37, wherein the first step etches a first layer of the substrate.

48. (Previously Presented) The method of claim 47, wherein the second step etches the first layer of the substrate.

49. (Previously Presented) The method of claim 47, wherein the second step etches a second layer of the substrate.

**RESPONSE ACCOMPANYING REQUEST FOR CONTINUED EXAMINATION**  
**Serial No. 10/672,002**  
**Page 4 of 6**

50. (Previously Presented) The method of claim 37, wherein the first gas is supplied to the first portion of the substrate through a first flow controller and to the second portion of the substrate through a second flow controller.

51. (Previously Presented) The method of claim 50, wherein the second gas is supplied to the first portion of the substrate through the first flow controller and to the second portion of the substrate through the second flow controller.

52. (Currently Amended) A method for etching a substrate, comprising:  
controlling the supply of a first etch gas to a first portion of the substrate through a first flow channel and to a second portion of the substrate through a second flow channel to etch the substrate during a first etch step, wherein the first portion is different than the second portion; and

controlling the supply of a second etch gas to the first portion of the substrate through the first flow channel and to the second portion of the substrate through the second flow channel during a second etch step, wherein the first etch step is different than the second etch step.

53. (Previously Presented) The method of claim 52, wherein the first gas is supplied to the first portion of the substrate through a first flow controller and to the second portion of the substrate through a second flow controller.

54. (Previously Presented) The method of claim 53, wherein the second gas is supplied to the first portion of the substrate through the first flow controller and to the second portion of the substrate through the second flow controller.